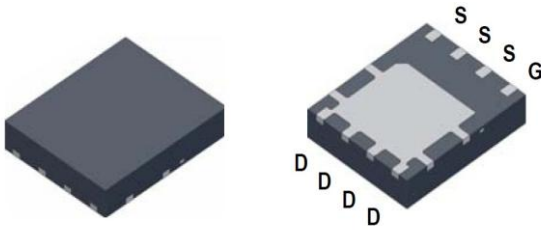


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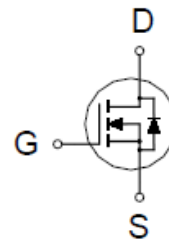
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	9m Ω @VGS = 10V	30A



PDFN 5*6P



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ²	$T_C = 25\text{ }^\circ\text{C}$ (Package Limited)	I_D	30	A
	$T_C = 25\text{ }^\circ\text{C}$ (Silicon Limited)		65	
	$T_C = 100\text{ }^\circ\text{C}$		41	
Pulsed Drain Current ¹		I_{DM}	150	
Continuous Drain Current ²	$T_A = 25\text{ }^\circ\text{C}$	I_D	13	
	$T_A = 70\text{ }^\circ\text{C}$		10	
Avalanche Current		I_{AS}	35	
Avalanche Energy	L = 0.1mH	E_{AS}	60	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	62.5	W
	$T_C = 100\text{ }^\circ\text{C}$		25	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	2.5	
	$T_A = 70\text{ }^\circ\text{C}$		1.6	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		50	

¹Pulse width limited by maximum junction temperature.

²Limited only by maximum temperature allowed

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

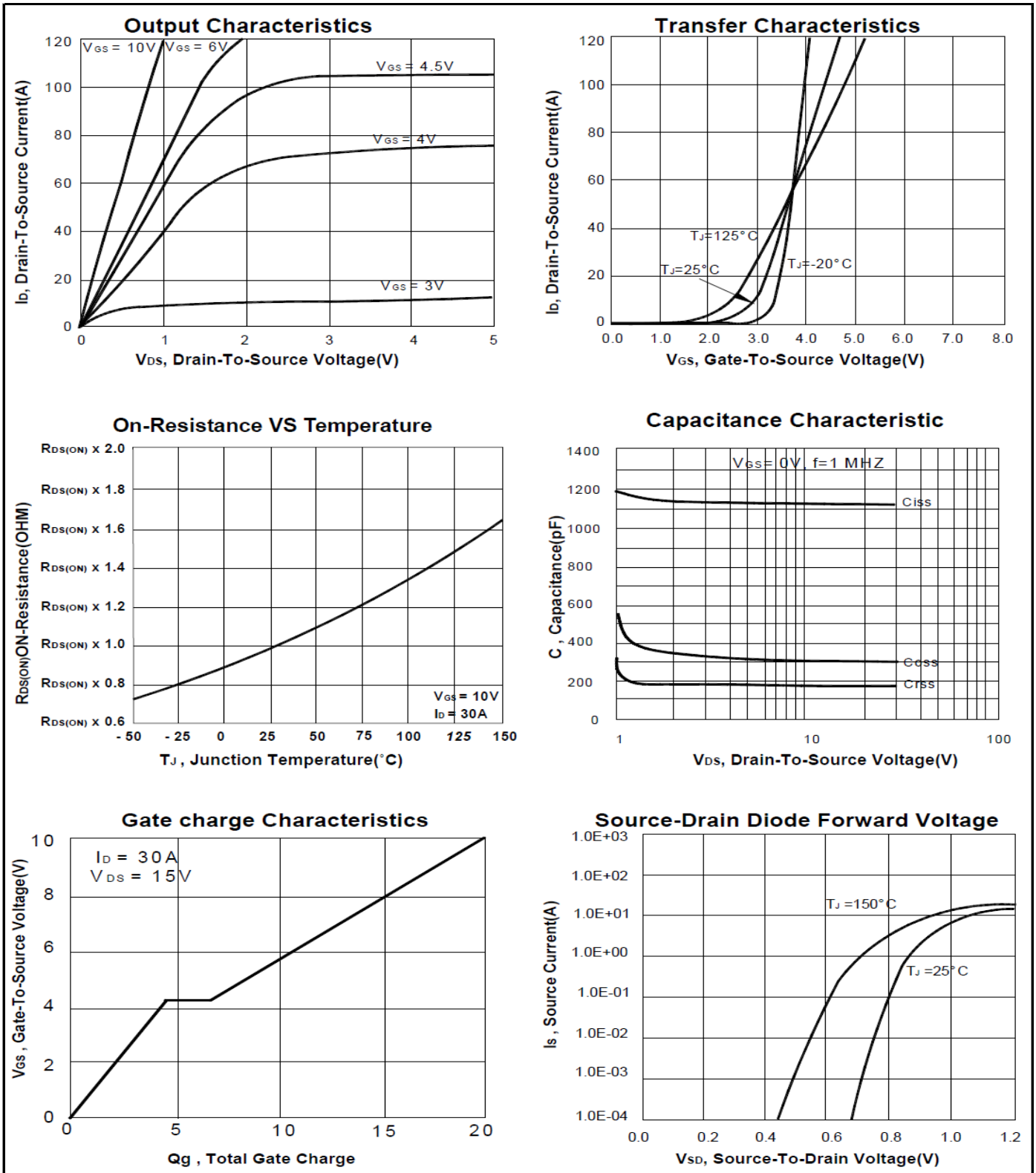
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.65	3	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±30V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V, T _J = 25 °C			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 55 °C			10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 15A		10	16	mΩ
		V _{GS} = 10V, I _D = 30A		6	9	
Forward Transconductance ¹	g _{fs}	V _{DS} = 15V, I _D = 17A		60		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		1140		pF
Output Capacitance	C _{oss}			299		
Reverse Transfer Capacitance	C _{riss}			178		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		1.49		Ω
Total Gate Charge ²	Q _g	V _{DD} = 15V, I _D = 30A, V _{GS} = 10V		22		nC
Gate-Source Charge ²	Q _{gs}			4.5		
Gate-Drain Charge ²	Q _{gd}			4		
Turn-On Delay Time ²	t _{d(on)}	V _{DD} = 15V, I _D = 10A, R _G = 6Ω		18		nS
Rise Time ²	t _r			10		
Turn-Off Delay Time ²	t _{d(off)}			35		
Fall Time ²	t _f			10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I _S				30	A
Forward Voltage ¹	V _{SD}	I _F = 30A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, di _F /dt = 100A /μS		30	5	nS

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

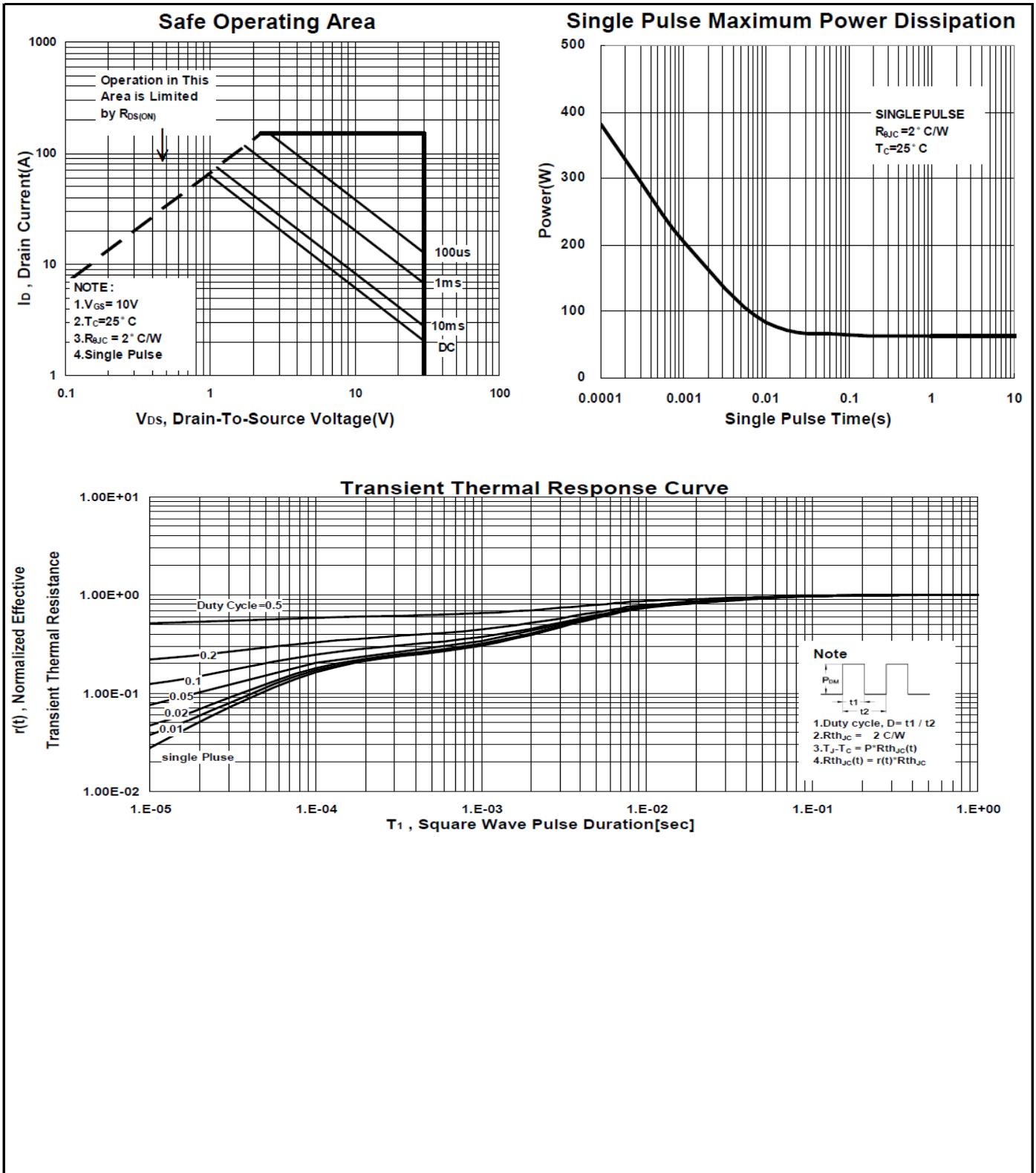
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Package Dimension

PDFN 5x6P MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8		5.15	J	3.33		3.78
B	5.44		5.9	K	0.9		
C	5.9		6.35	L	0.35		0.712
D	0.33		0.51	M	0°		12°
E		1.27		N	4.8		5.5
F	0.8		1.25	O	0.05		0.3
G	0.15		0.34	P	0.06		0.2
H	3.61		4.31	S	3.69		4.19
I	0.35		0.71				

